

(AMENDED)

Substrate
道@p=DBR Active Region

Fig. 1 -- (Prior Art.) --



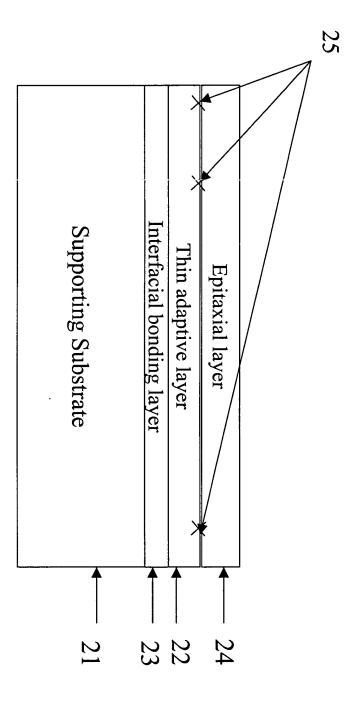


Fig. 2 -- 20 --



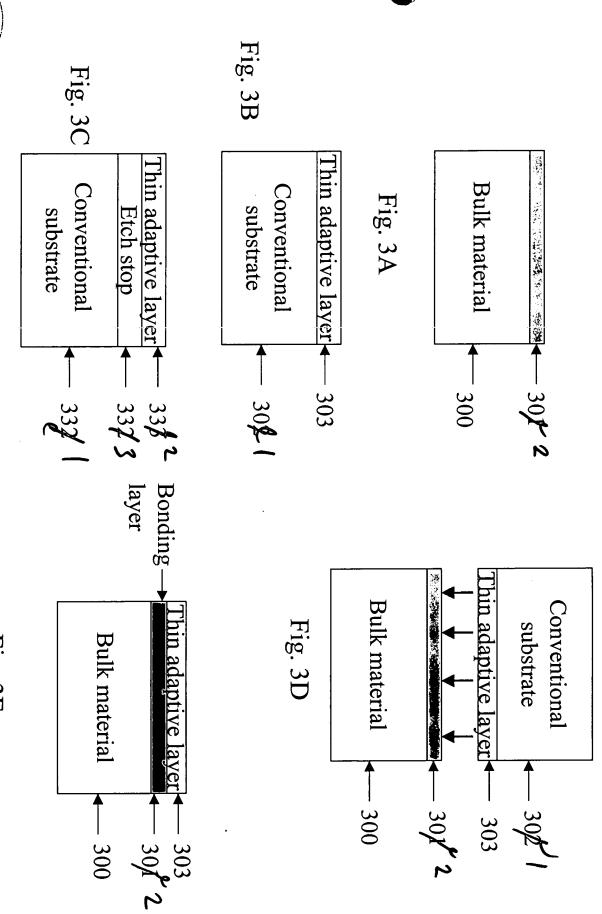
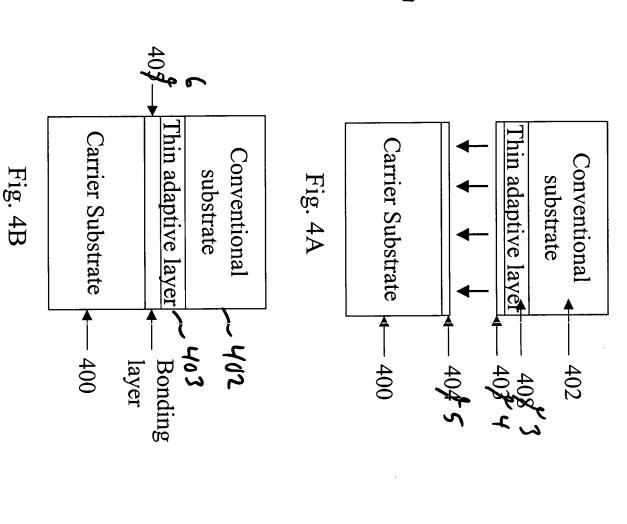
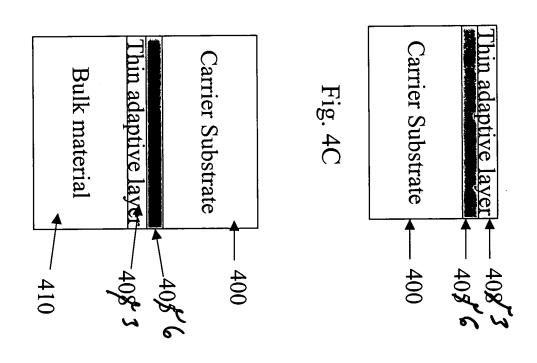


Fig. 3E



Fig. 4D







epi Side Down

epi Side Up

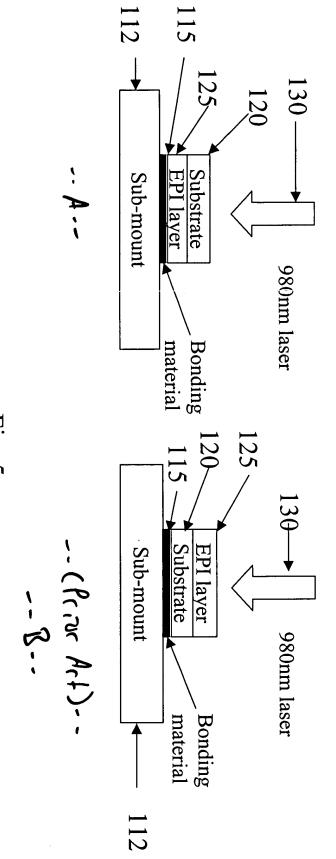


Fig. 5



Substrate	Boutonnedisk	Active Region	

Fig. 1 (Prior Art)



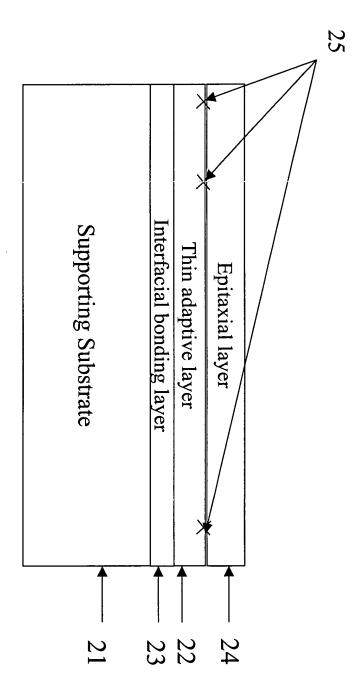
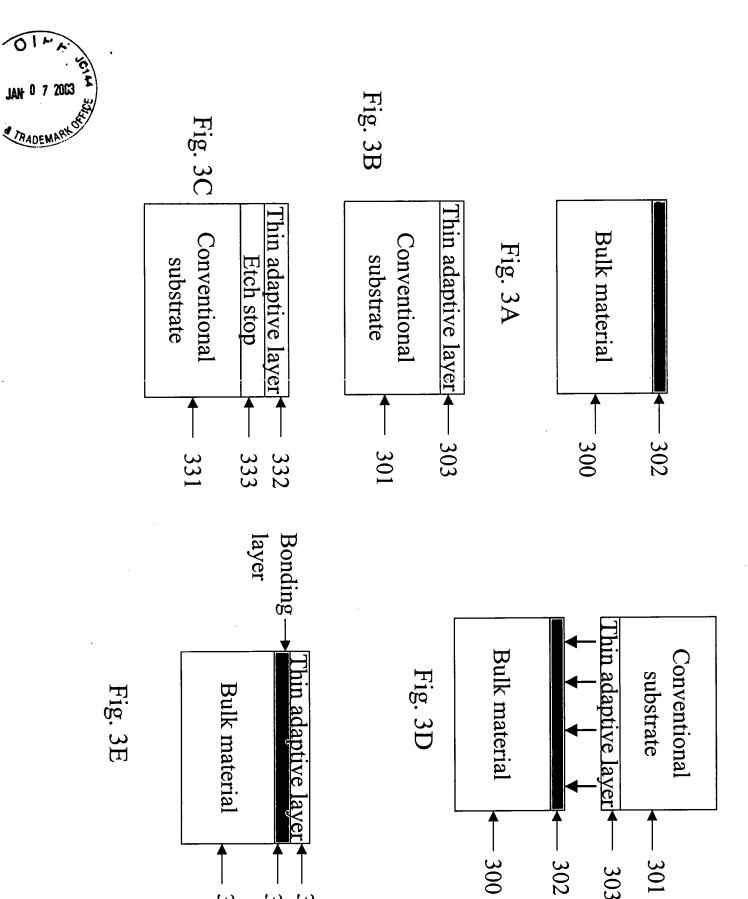


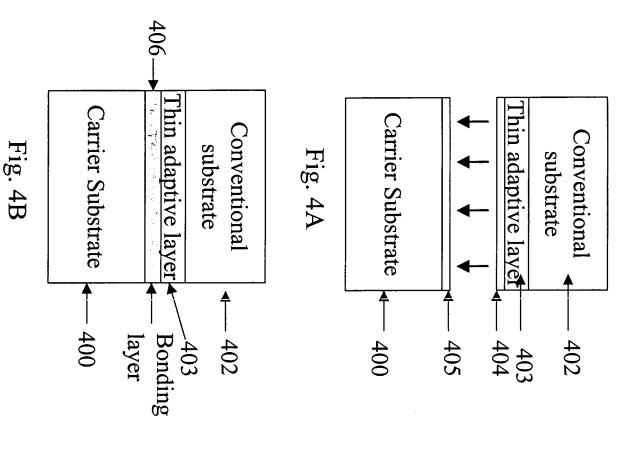
Fig. 2 <u>20</u>



- 300

- 303





Chin adaptive layer

Carrier Substrate

- 400

406

403

Fig. 4C

Carrier Substrate
406
Thin adaptive layer
403
Bulk material
410

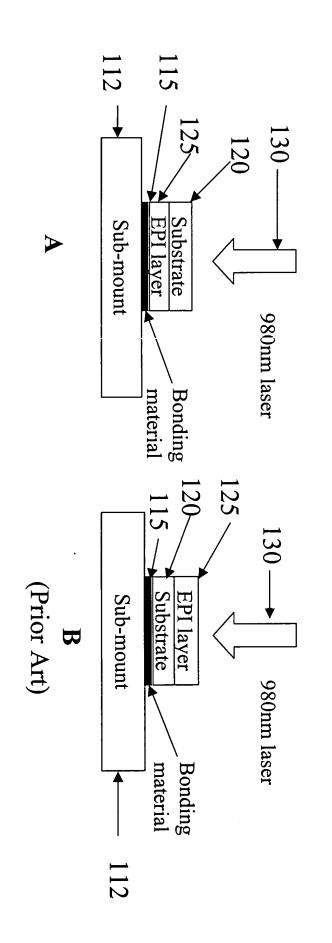
Fig. 4D



Fig. 5

epi Side Down

epi Side Up





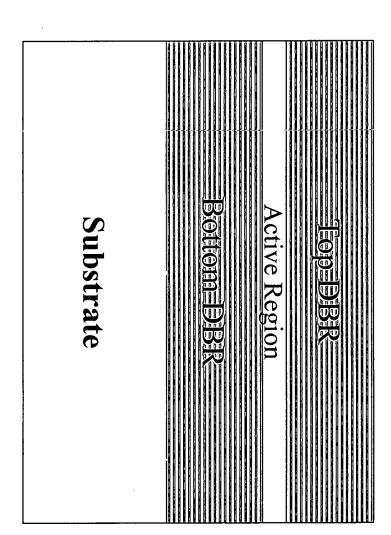


Fig. 1 (Prior Art)



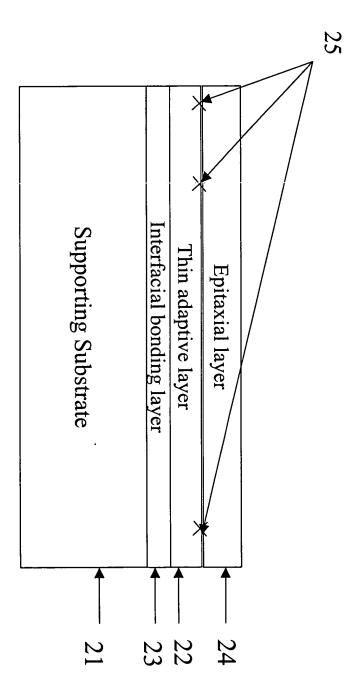


Fig. 2 <u>20</u>



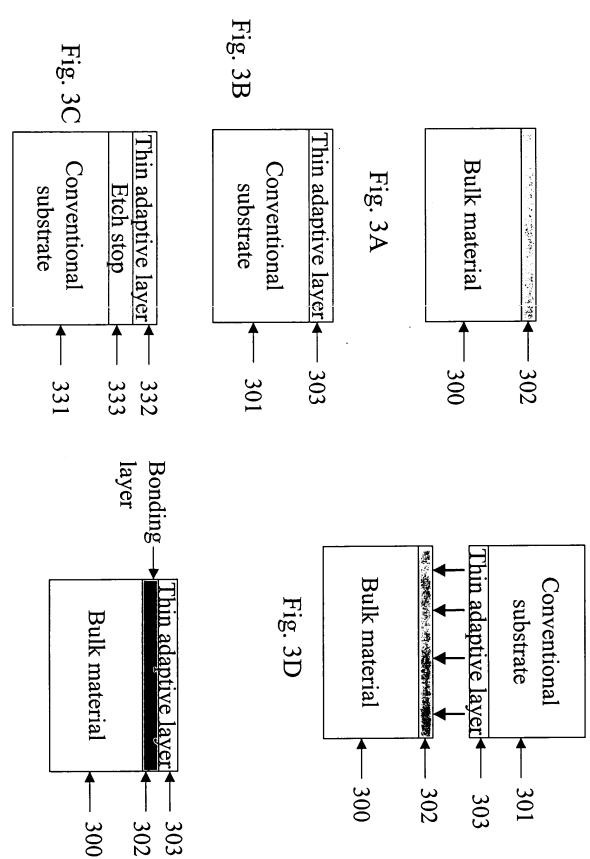
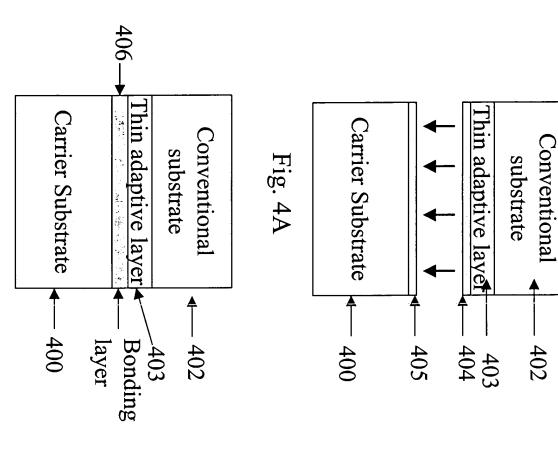


Fig. 3E



Fig. 4B



Thin adaptive layer 403
406
Carrier Substrate 400

Fig. 4C

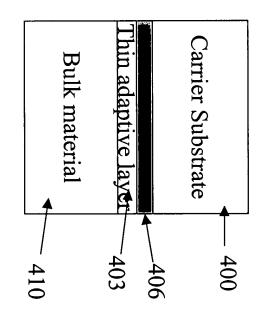


Fig. 4D



Fig. 5
epi Side Døwn

epi Side Up

